

3. (Amended) A method as claimed in claim 1, wherein said substance liquid at the room temperature under the atmospheric pressure is an organic metal compound.

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A 4. (Amended) A method as claimed in claim 1, wherein said substance liquid at the room temperature under the atmospheric pressure is  $\text{Ti}(\text{i} - \text{OC}_3\text{H}_7)_4$ .

5. (Amended) A method as claimed in claim 1, wherein said pressurized gas is an inert gas or a reactive gas.

6. (Amended) A method as claimed in claim 1, wherein said nozzle is an expansion-type nozzle.

7. (Amended) A method for forming gas cluster ions, which comprises the step of ionizing the gas cluster formed by the method as claimed in claim 1.

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A 9. (Amended) A method for forming a thin film, which comprises the step of irradiating the cluster ions formed by the method as claimed in claim 7 onto a substrate surface, thereby forming a thin film.

13. (Amended) A method for forming a thin film as claimed in claim 11, wherein an oxide film is deposited by irradiating cluster ions of a gas containing oxygen and at least an organic metal compound gas onto the substrate surface.

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A 14. (Amended) A method for forming a thin film as claimed in claim 11, which comprises the steps of irradiating oxygen gas cluster ions onto the substrate, and at the same time, or alternately, irradiating a single, or a plurality of, component gas of deposit film onto the substrate surface to cause reaction of the both, thereby depositing a thin ferroelectric film on the substrate surface.

17. (Amended) A method for forming an oxygen-containing gas cluster, which comprises the step of ionizing the gas cluster formed by the method as claimed in claim 15.